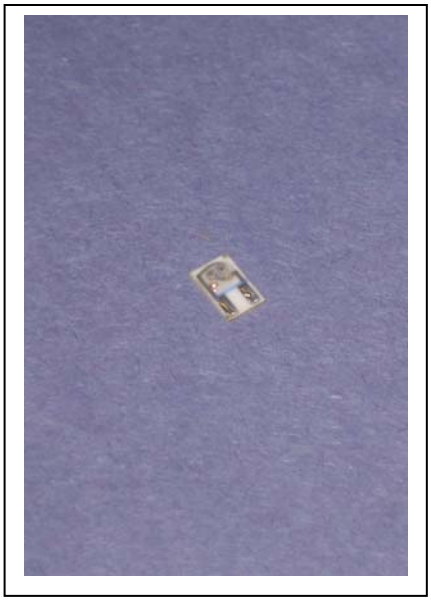
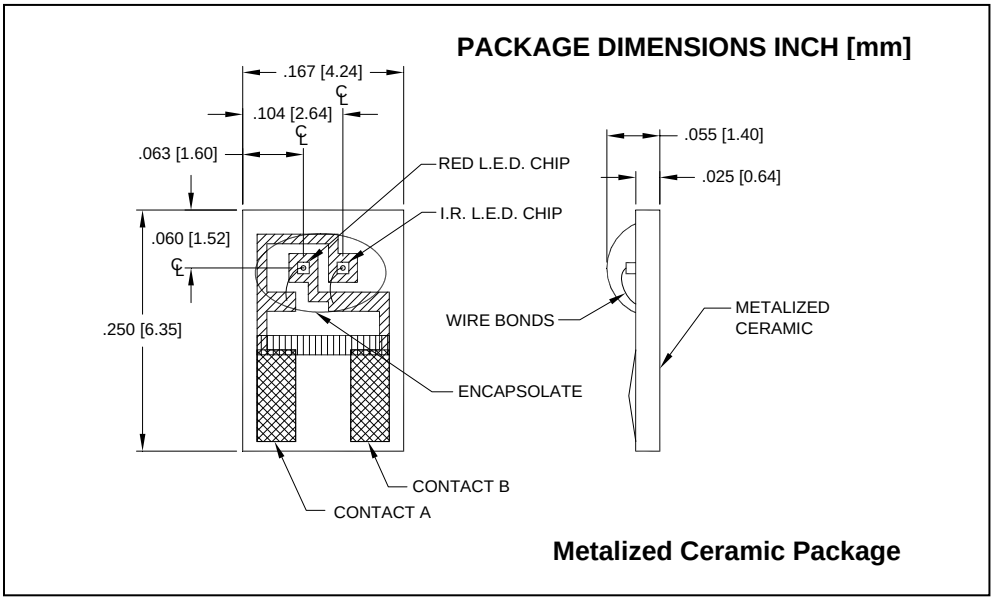
GaAlAs High power IR LED Emitters
(660nm/905nm) PDI-E832





FEATURES

- Low Cost
- 660 nm +/- 3nm
- 2 drive line

DESCRIPTION

The **PDI-E832** is a two drive line dual emitter oximeter component. The 660 and 905 nm GaAlAs infrared emitters are mounted in a glob toped. The LEDs are bias separately by alternating polarity on the bias pins.

APPLICATIONS

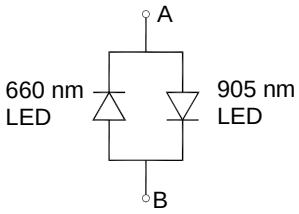
- Oximeter Probes
- Finger Clamps
- Reusable probes

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
P_d	Power Dissipation		250	mW
I_f	Continuous Forward Current		30	mA
I_p	Peak Forward Current		200	mA
V_r	Reverse Voltage		4	V
T_{STG}	Storage Temperature	-40	+80	°C
T_O	Operating Temperature	-40	+80	°C
T_S	Soldering Temperature*		+240	°C

* For 3 seconds max using a heat sink

SCHEMATIC



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	660 nm			905 nm			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
P_o	Radiant Flux	I_f = 20 mA	1.8	2.4		1.2	1.8		mW
Iv	Luminous Intensity	I_f= 20 mA	20	30					mcd
V_f	Forward Voltage	I_f = 20 mA		1.8	2.4		1.2	1.5	V
λ_p	Peak Wavelength	I_f = 20 mA	658	661	664	895	905	915	nm
$\Delta\lambda$	Spectral Halfwidth	I_f = 20 mA		25			50		nm
t_r	Rise Time	I_f = 20 mA		0.1			1.4		uS
t_f	Fall Time	I_f = 20 mA		0.04			0.7		uS

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.

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